

MKA06N046L

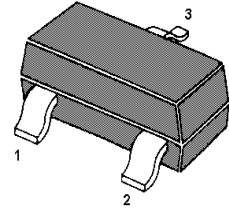
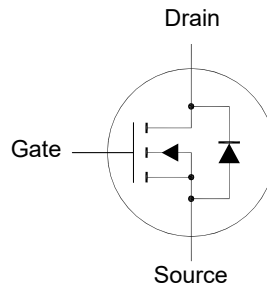
N-Channel Enhancement Mode MOSFET

Features

- Extremely low threshold voltage

Applications

- Portable appliances
- Battery management
- High speed switch



1. Gate 2. Source 3. Drain
SOT-23 Plastic Package

Absolute Maximum Ratings ($T_a = 25^\circ\text{C}$)

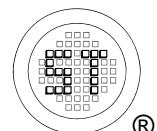
Parameter	Symbol	Value	Unit
Drain-Source Voltage	V_{DS}	60	V
Gate-Source Voltage	V_{GS}	± 20	V
Drain Current	I_D	4	A
Peak Drain Current, Pulsed ¹⁾	I_{DM}	20	A
Power Dissipation ²⁾	P_D	1.38	W
Operating Junction and Storage Temperature Range	T_J, T_{stg}	- 55 to + 150	$^\circ\text{C}$

Thermal Resistance Ratings

Parameter	Symbol	Max.	Unit
Thermal Resistance from Junction to Ambient ²⁾ $t \leq 10$ s Steady State	$R_{\theta JA}$	90 166	$^\circ\text{C/W}$

¹⁾ Pulse width $\leq 10 \mu\text{s}$, duty cycle $\leq 1\%$.

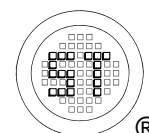
²⁾ Device mounted on FR-4 substrate PC board, 2oz copper, with 1-inch square copper plate in still air.



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Characteristics at $T_a = 25^\circ\text{C}$ unless otherwise specified

Parameter	Symbol	Min.	Typ.	Max.	Unit
STATIC PARAMETERS					
Drain-Source Breakdown Voltage at $I_D = 250 \mu\text{A}$	$V_{(BR)DSS}$	60	-	-	V
Zero Gate Voltage Drain Current at $V_{DS} = 48 \text{ V}$	I_{DSS}	-	-	1	μA
Gate-Source Leakage at $V_{GS} = \pm 20 \text{ V}$	I_{GSS}	-	-	± 100	nA
Gate-Source Threshold Voltage at $V_{DS} = V_{DS}, I_D = 250 \mu\text{A}$	$V_{GS(th)}$	1.2	-	2.5	V
Drain-Source On-State Resistance at $V_{GS} = 10 \text{ V}, I_D = 4 \text{ A}$ at $V_{GS} = 4.5 \text{ V}, I_D = 3 \text{ A}$	$R_{DS(on)}$	- -	- -	34 46	m Ω
DYNAMIC PARAMETERS					
Gate resistance at $V_{DS} = 0 \text{ V}, V_{GS} = 0 \text{ V}, f = 1 \text{ MHz}$	R_g	-	0.8	-	Ω
Input Capacitance at $V_{DS} = 30 \text{ V}, V_{GS} = 0 \text{ V}, f = 1 \text{ MHz}$	C_{iss}	-	1087	-	pF
Output Capacitance at $V_{DS} = 30 \text{ V}, V_{GS} = 0 \text{ V}, f = 1 \text{ MHz}$	C_{oss}	-	47	-	pF
Reverse Transfer Capacitance at $V_{DS} = 30 \text{ V}, V_{GS} = 0 \text{ V}, f = 1 \text{ MHz}$	C_{rss}	-	43	-	pF
Total Gate Charge at $V_{DS} = 30 \text{ V}, I_D = 4 \text{ A}, V_{GS} = 10 \text{ V}$	Q_g	-	19	-	nC
Gate Source Charge at $V_{DS} = 30 \text{ V}, I_D = 4 \text{ A}, V_{GS} = 10 \text{ V}$	Q_{gs}	-	4.7	-	nC
Gate Drain Charge at $V_{DS} = 30 \text{ V}, I_D = 4 \text{ A}, V_{GS} = 10 \text{ V}$	Q_{gd}	-	2.6	-	nC
Turn-On Delay Time at $V_{DS} = 30 \text{ V}, I_D = 4 \text{ A}, V_{GS} = 10 \text{ V}, R_G = 3.3 \Omega$	$t_{d(on)}$	-	10	-	ns
Turn-On Rise Time at $V_{DS} = 30 \text{ V}, I_D = 4 \text{ A}, V_{GS} = 10 \text{ V}, R_G = 3.3 \Omega$	t_r	-	21	-	ns
Turn-Off Delay Time at $V_{DS} = 30 \text{ V}, I_D = 4 \text{ A}, V_{GS} = 10 \text{ V}, R_G = 3.3 \Omega$	$t_{d(off)}$	-	9	-	ns
Turn-Off Fall Time at $V_{DS} = 30 \text{ V}, I_D = 4 \text{ A}, V_{GS} = 10 \text{ V}, R_G = 3.3 \Omega$	t_f	-	2	-	ns
Body-Diode PARAMETERS					
Drain-Source Diode Forward Voltage at $V_{GS} = 0 \text{ V}, I_S = 1 \text{ A}$	V_{SD}	-	-	1.3	V
Body-Diode Continuous Current	I_S	-	-	4	A
Body Diode Reverse Recovery Time at $I_S = 4 \text{ A}, di/dt = 100 \text{ A}/\mu\text{s}$	t_{rr}	-	8.3	-	ns
Body Diode Reverse Recovery Charge at $I_S = 4 \text{ A}, di/dt = 100 \text{ A}/\mu\text{s}$	Q_{rr}	-	4.9	-	nC



Electrical Characteristics Curves

Fig. 1 Typical Output Characteristics

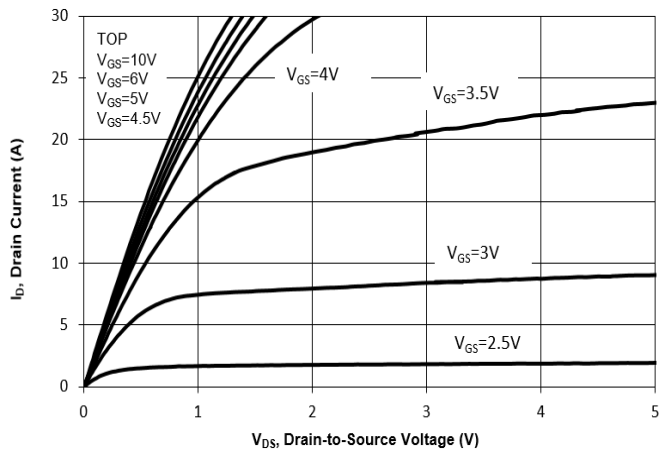


Fig. 2 Typical Transfer Characteristics

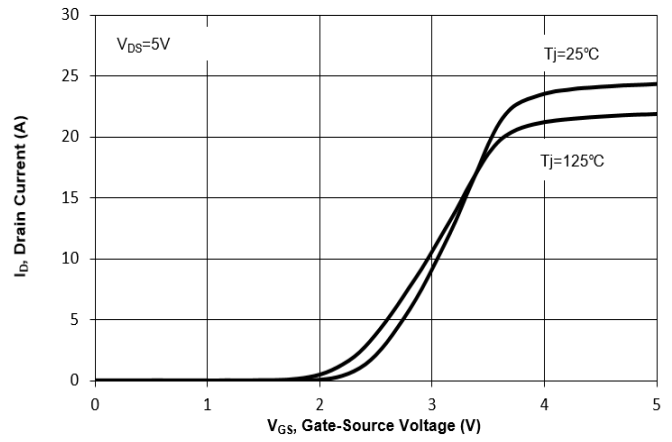


Fig. 3 On-Resistance vs. Drain Current

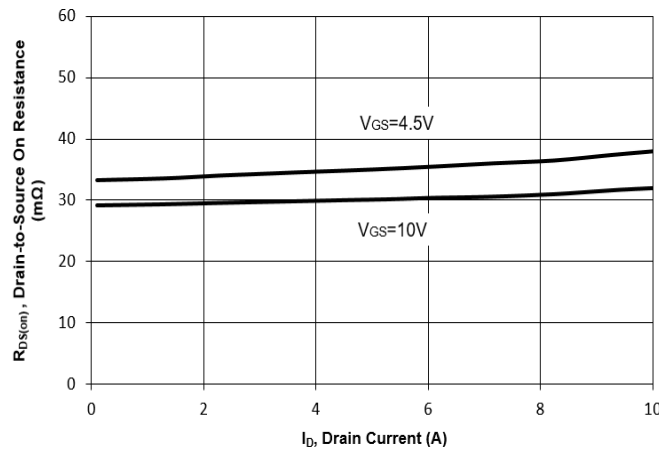


Fig. 4 On-Resistance vs. Gate Voltage

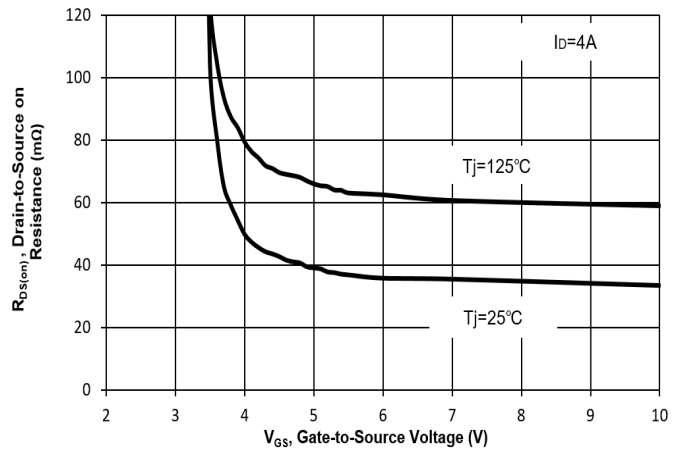


Fig. 5 On-Resistance vs. Tj

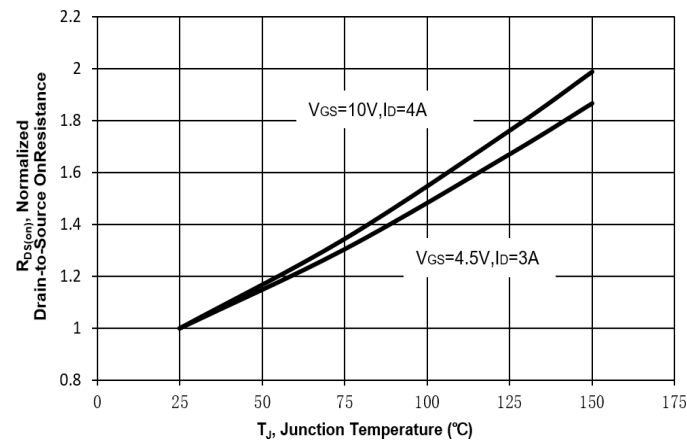
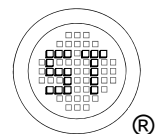
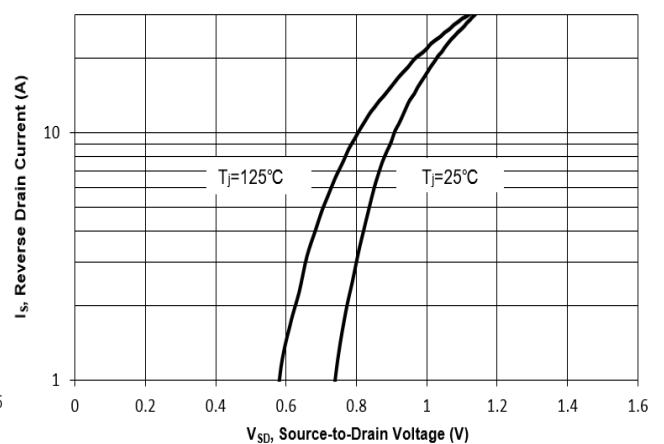


Fig. 6 Typical Body-Diode Forward Characteristics



Electrical Characteristics Curves

Fig. 7 Typical Junction Capacitance

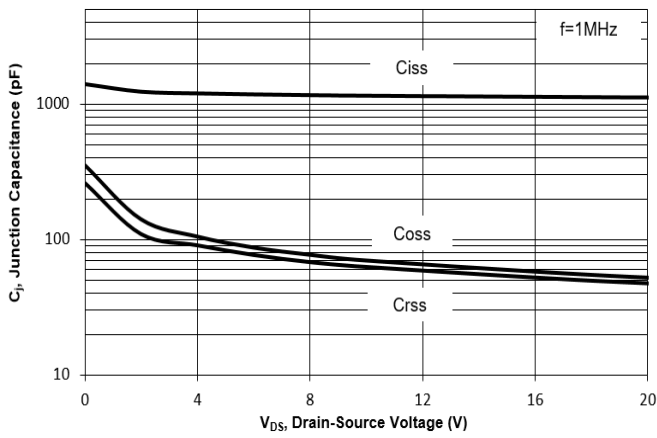


Fig. 8 Drain-Source Leakage Current vs. Tj

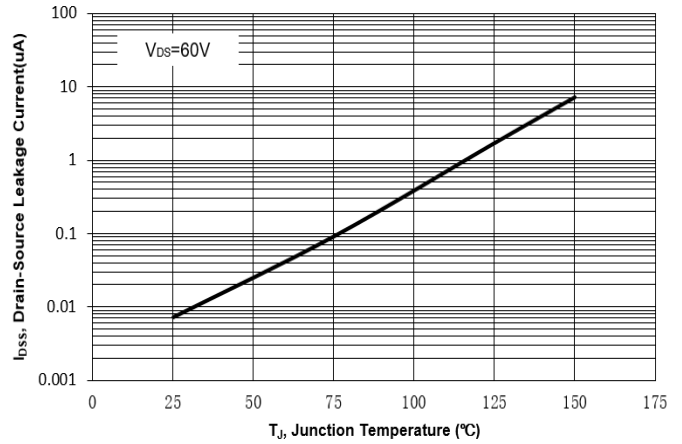


Fig. 9 V(BR)DSS vs. Junction Temperature

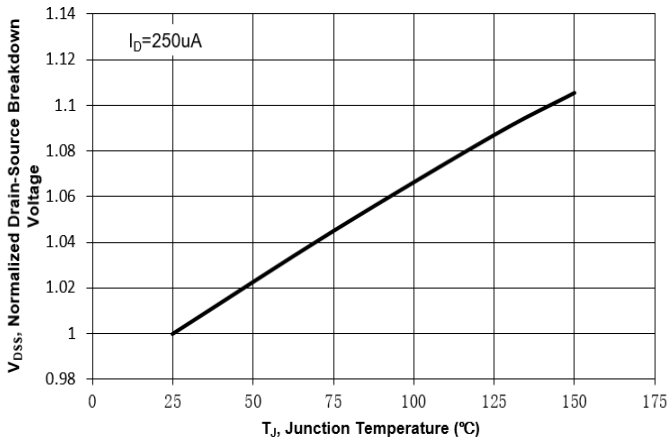


Fig. 10 Gate Threshold Variation vs. Tj

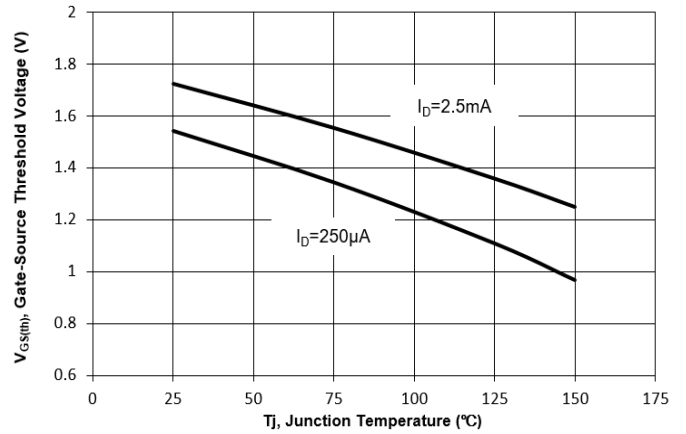
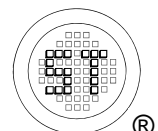
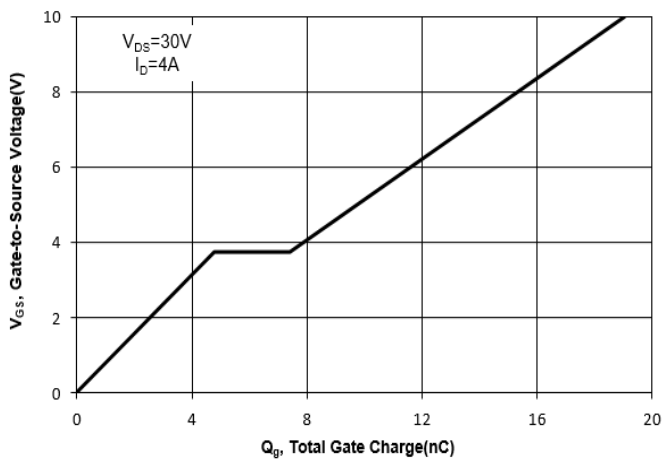


Fig. 11 Gate Charge



Test Circuits

Fig.1-1 Switching times test circuit

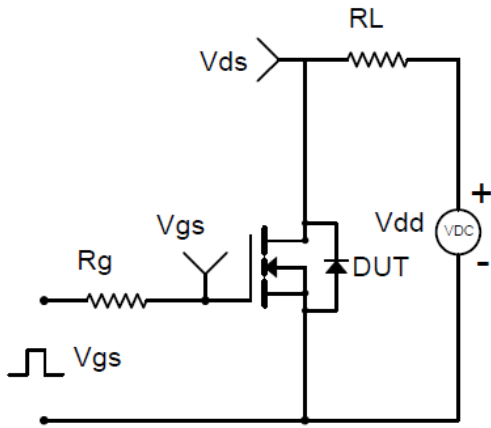


Fig.1-2 Switching Waveform

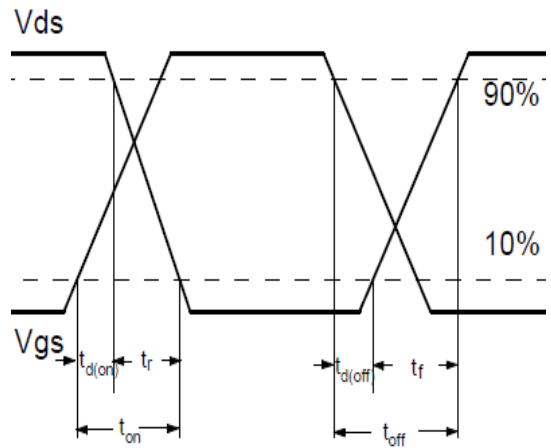


Fig.2-1 Gate charge test circuit

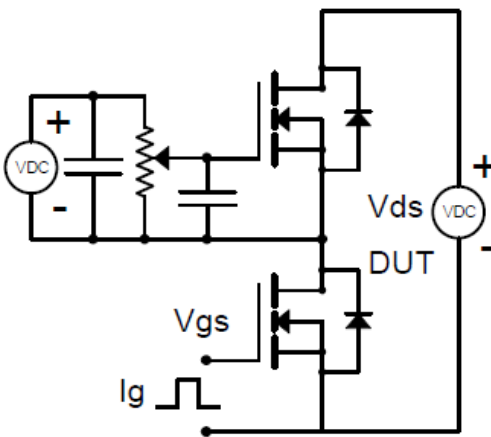
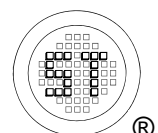
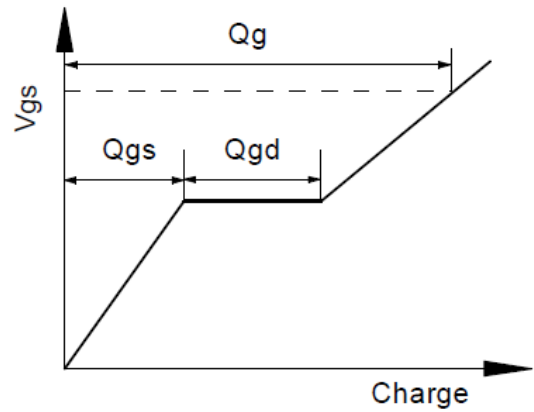


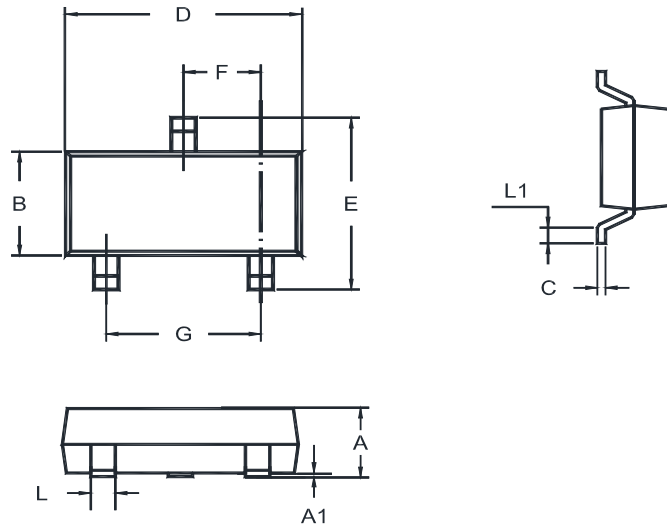
Fig.2-2 Gate charge waveform



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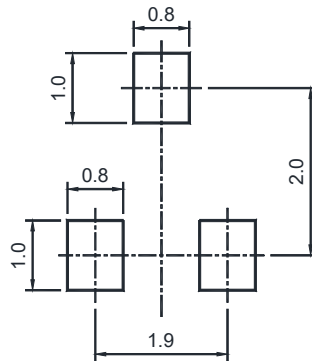
Package Outline (Dimensions in mm)

SOT-23



Unit	A	A1	B	C	D	E	F	G	L	L1
mm	1.20	0.100	1.40	0.19	3.04	2.6	1.02	2.04	0.51	0.2
	0.89	0.013	1.20	0.08	2.80	2.2	0.89	1.78	0.37	MIN

Recommended Soldering Footprint



Packing information

Package	Tape Width (mm)	Pitch		Reel Size		Per Reel Packing Quantity
		mm	inch	mm	inch	
SOT-23	8	4 ± 0.1	0.157 ± 0.004	178	7	3,000

Marking information

" LK " = Part No.
 " YM " = Date Code Marking
 " Y " = Year
 " M " = Month
 Font type: Arial

